

# **An 8-bit Analog-to-Digital Converter based on the Voltage-Dependent Switching Probability of a Magnetic Tunnel Junction**

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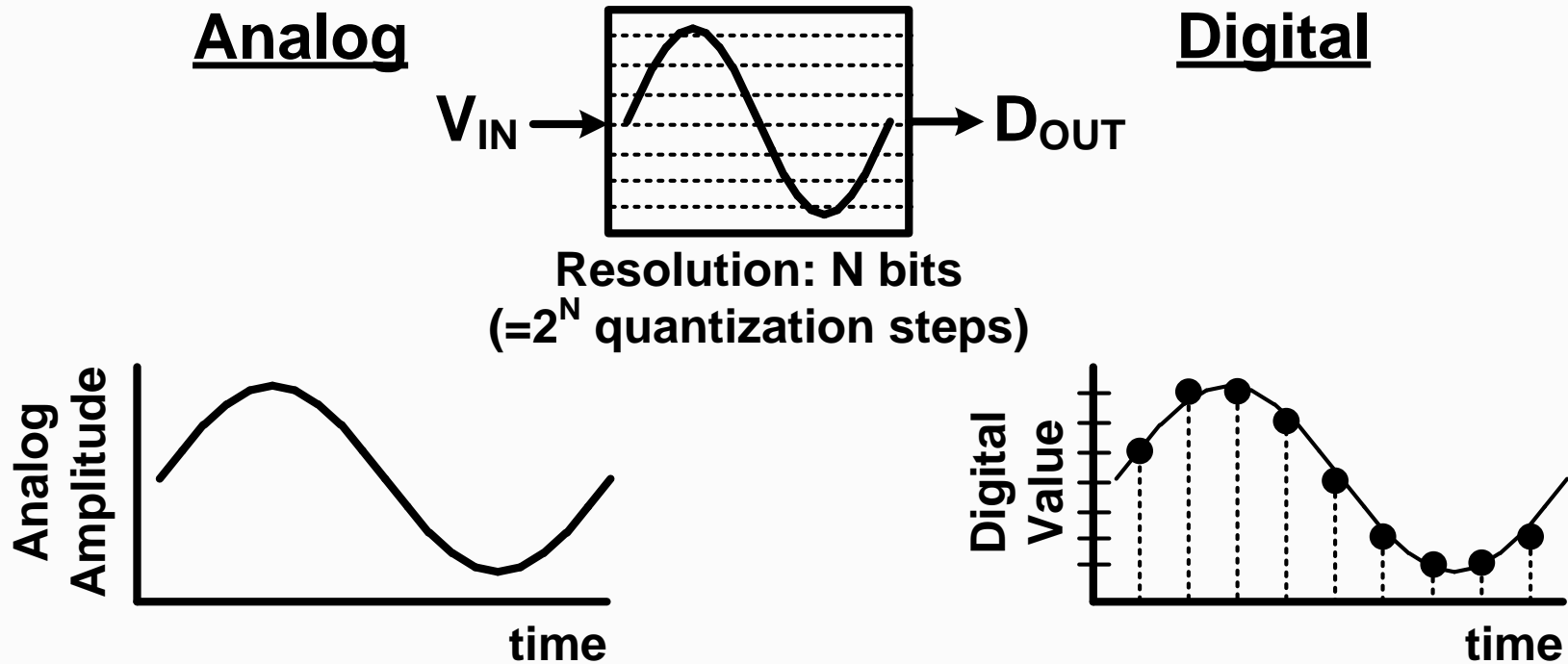
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# Outline

- **Background**
  - Analog-to-Digital Converter (ADC)
  - Magnetic Tunnel Junction (MTJ)
- **Proposed MTJ-based “Probabilistic” ADC**
- **Techniques for Improving Linearity and Input Voltage Range**
- **Summary**

# Analog-to-Digital Converter (ADC)

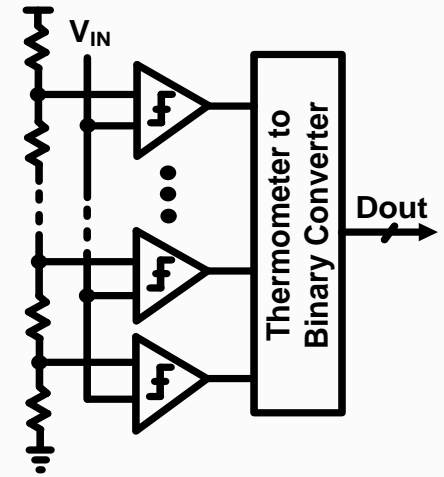


- ADC converts an analog input voltage to a digital code
- An N-bit ADC quantizes an analog voltage into  $2^N$  discrete levels

# Traditional ADC Architectures

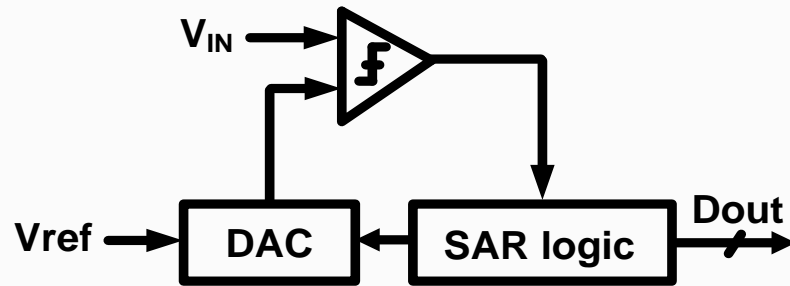
- **Flash ADC**

- Fast conversion rate (up to several Gs/s)
- High power consumption
- Low resolution (2 ~ 8 bit)

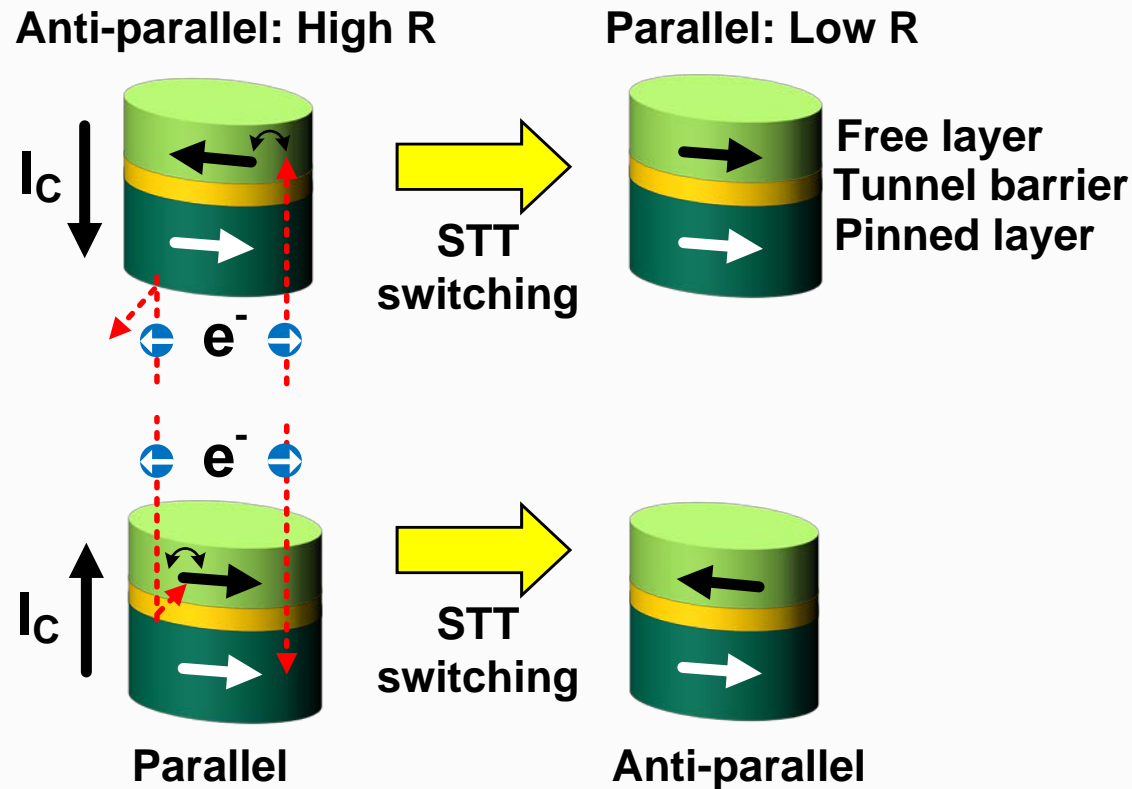


- **Successive Approximation Register (SAR) ADC**

- High resolution (10 ~ 16 bit)
- Low power consumption
- Slow conversion rate (1Ks/s ~ several 100Ms/s)



# Magnetic Tunnel Junction (MTJ)

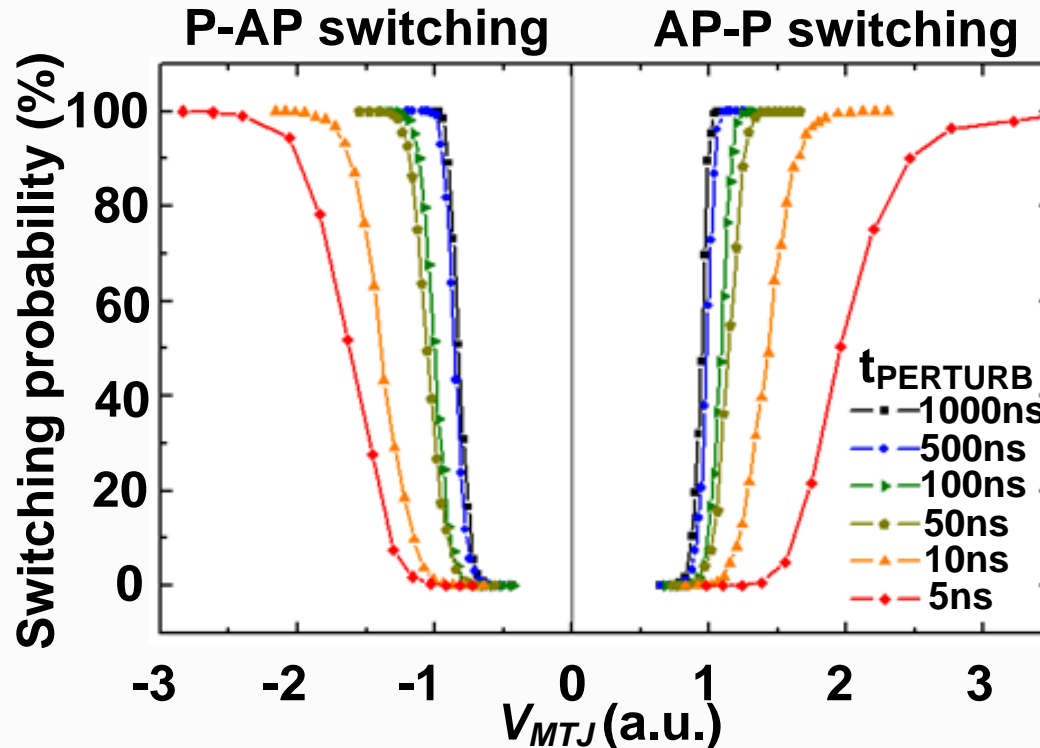


- Basic storage element of STT-MRAM memory
- Spin polarized electrons rotate the magnetization of free layer using spin transfer torque

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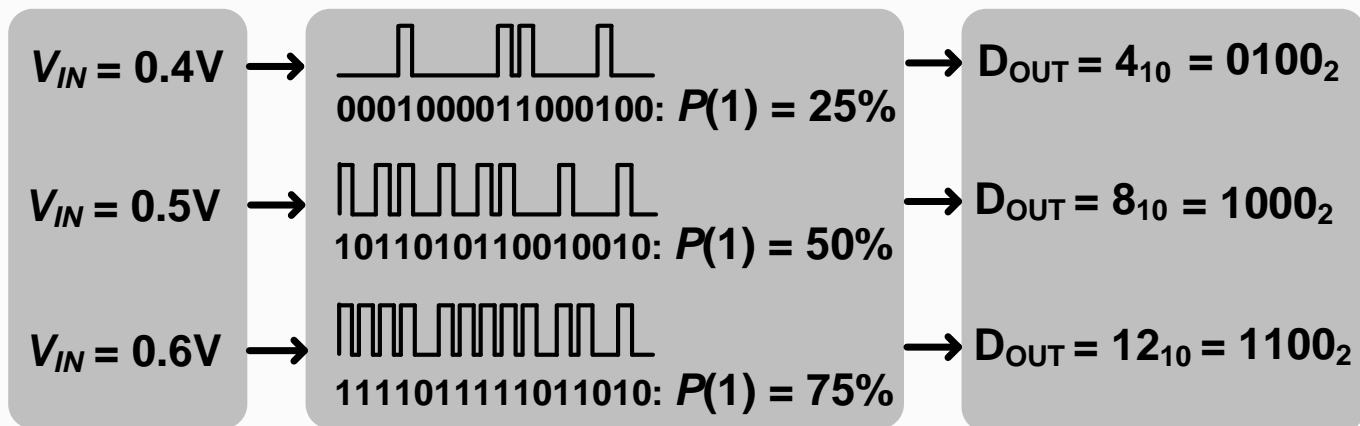
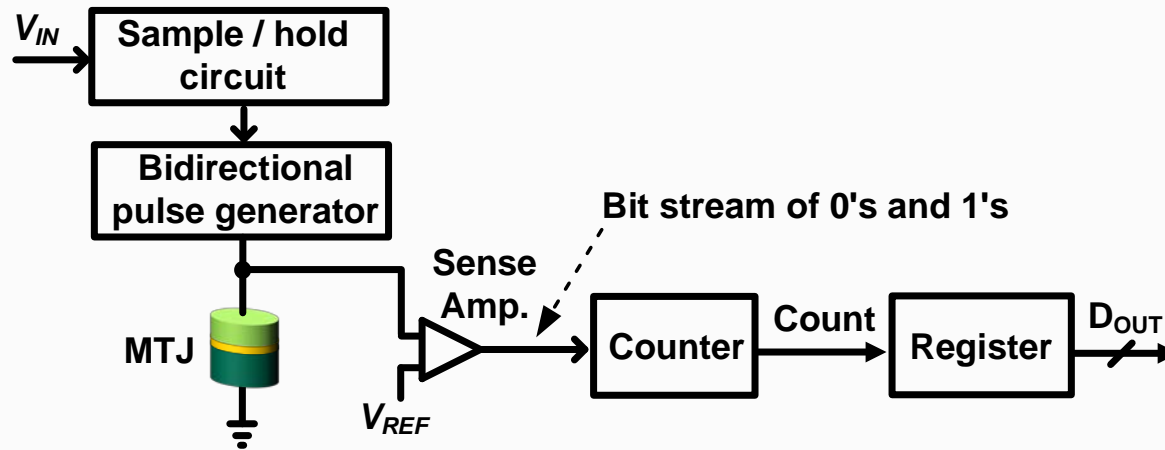
# Switching Probability of an MTJ



H. Zhao, et al., TMAG, 2012.

- **Switching probability depends on the applied analog voltage ( $V_{MTJ}$ )**

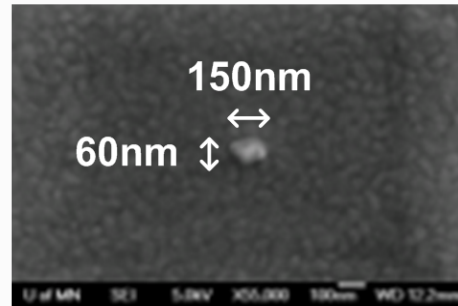
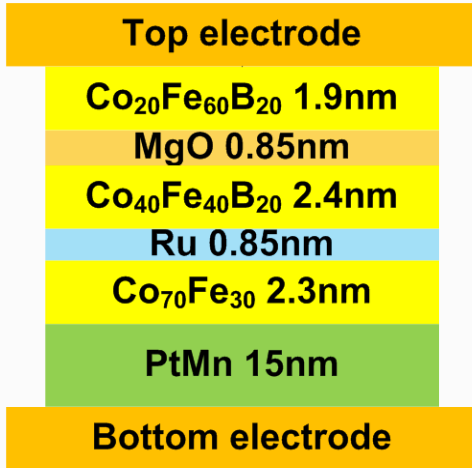
# Proposed MTJ-Based “Probabilistic” ADC



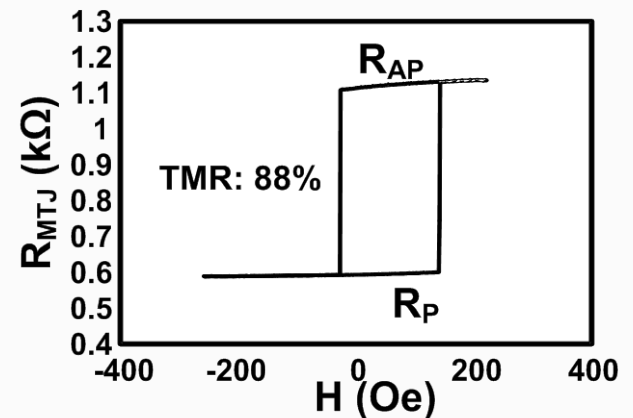
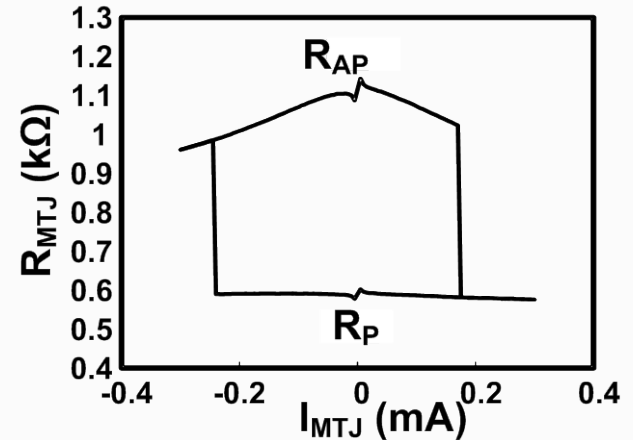
- Analog voltage  $\rightarrow$  random bit stream  $\rightarrow$  compute probability of ‘1’s  $\rightarrow$  digital code



# MTJ Device Used for Experiments

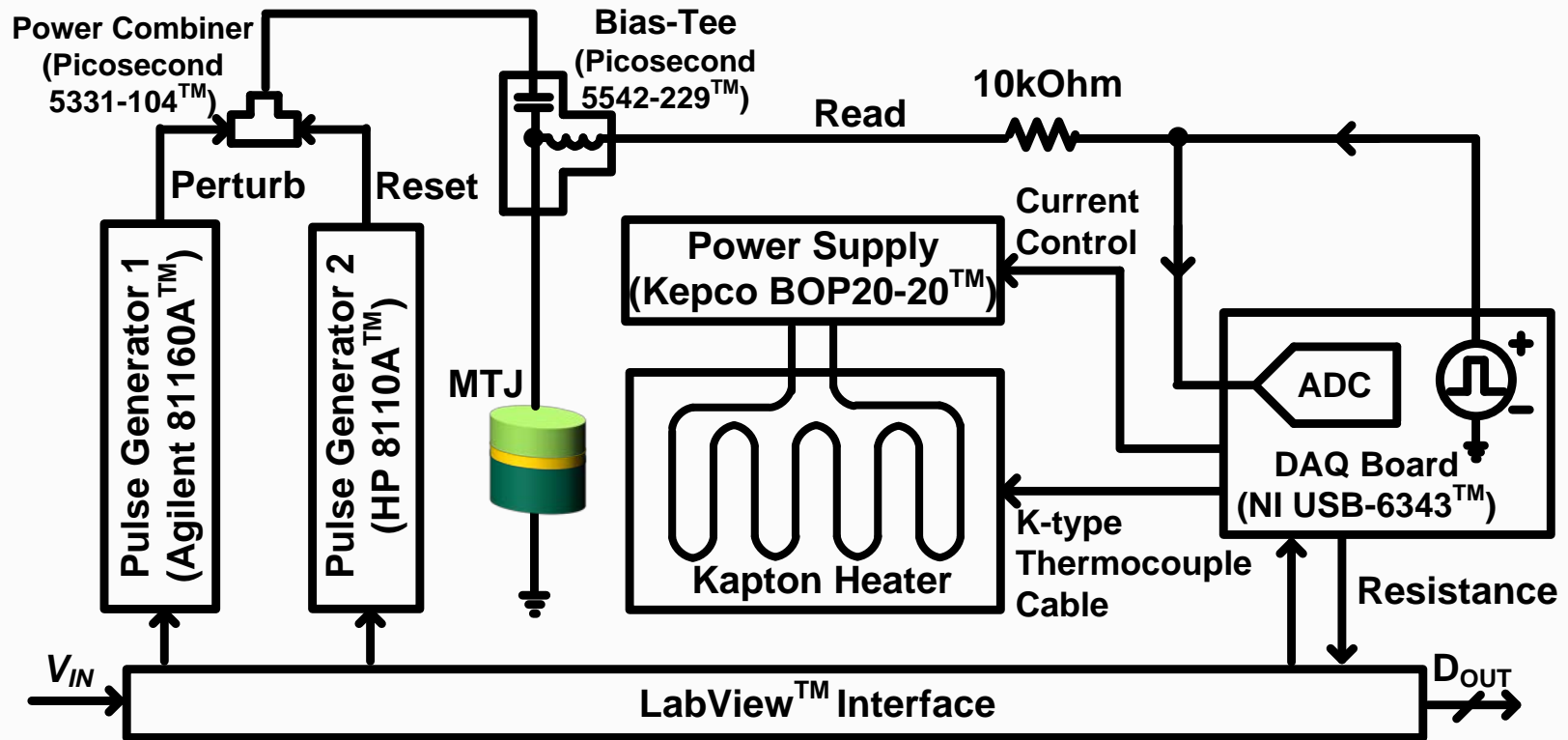


Dimension	150x60nm <sup>2</sup>
RA	5.31 Ω·μm <sup>2</sup>
TMR	88%
Thermal stability	64



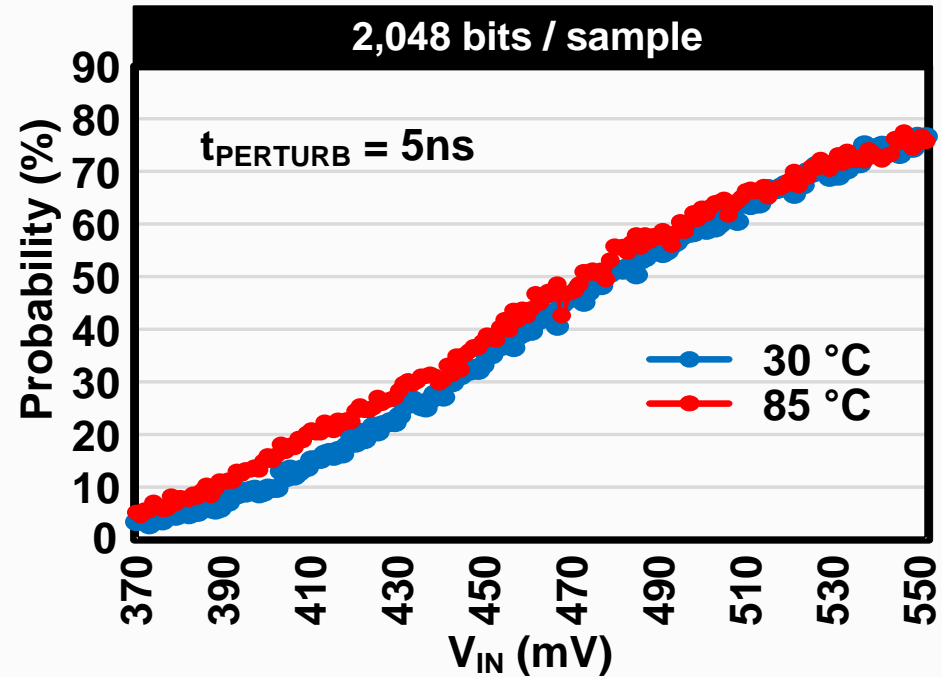
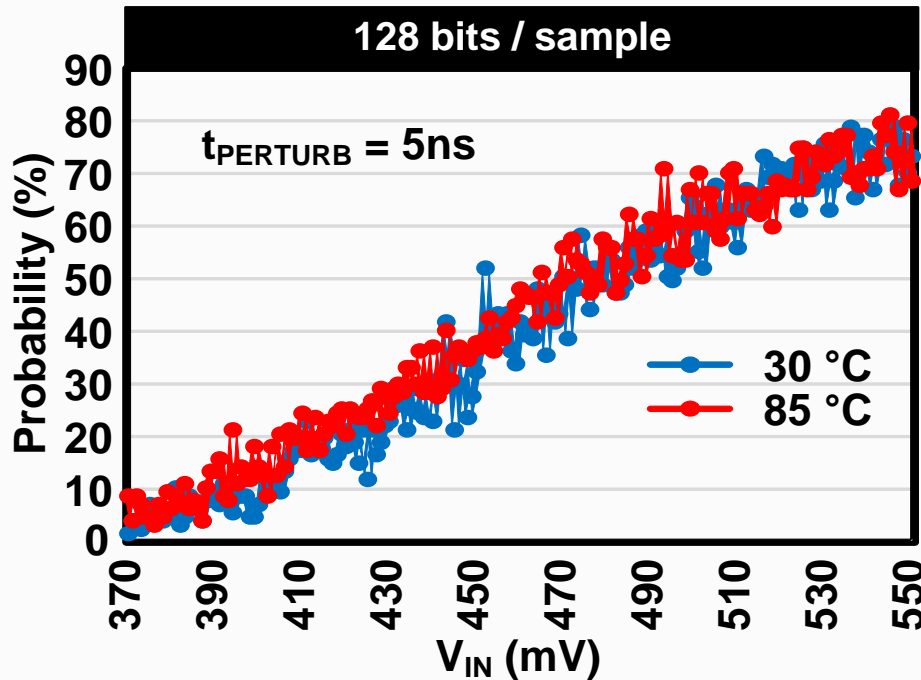
- **CoFeB based in-plane MTJ device with a TMR of 88% and a thermal stability of 64**

# Experimental Setup



- MTJ measurement setup with 1mV voltage resolution and  $<1$  °C temperature accuracy

# Measured Switching Probability Curve

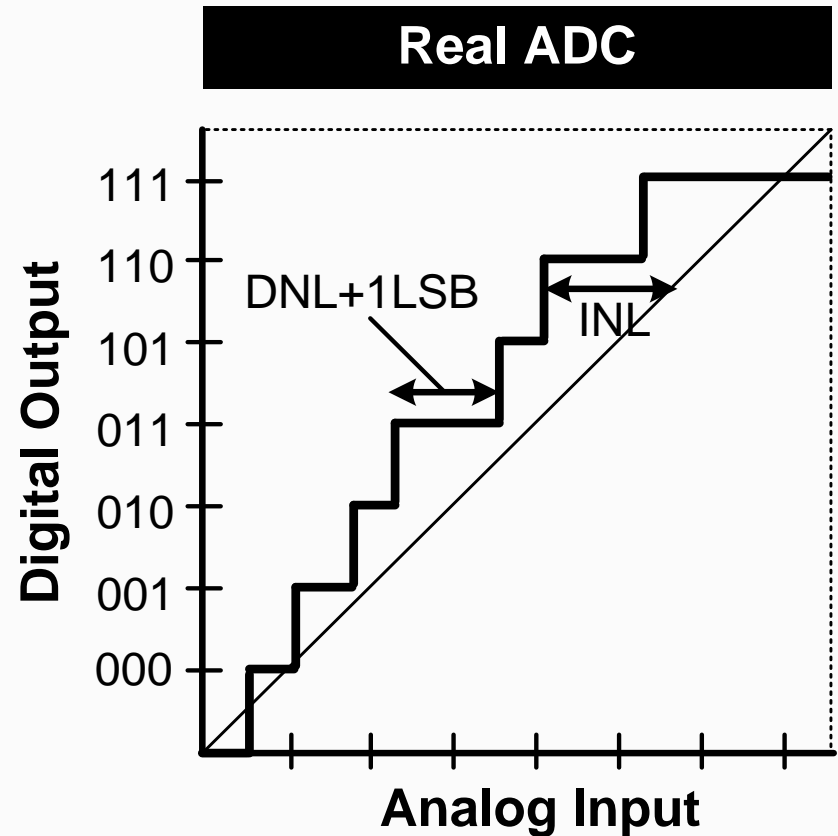
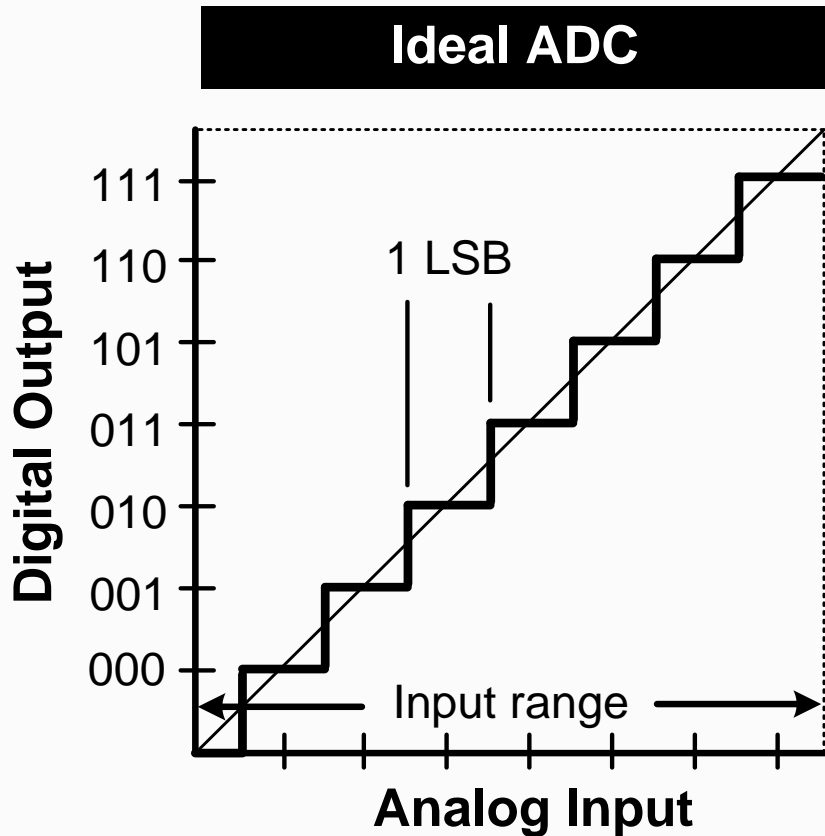


- A short 5ns  $t_{\text{PERTURB}}$  used for suppressing thermal activation switching
- Averaging more bits gives a smoother and more accurate probability curve (128 bits vs. 2,048 bits)
- Temperature sensitivity is acceptably low

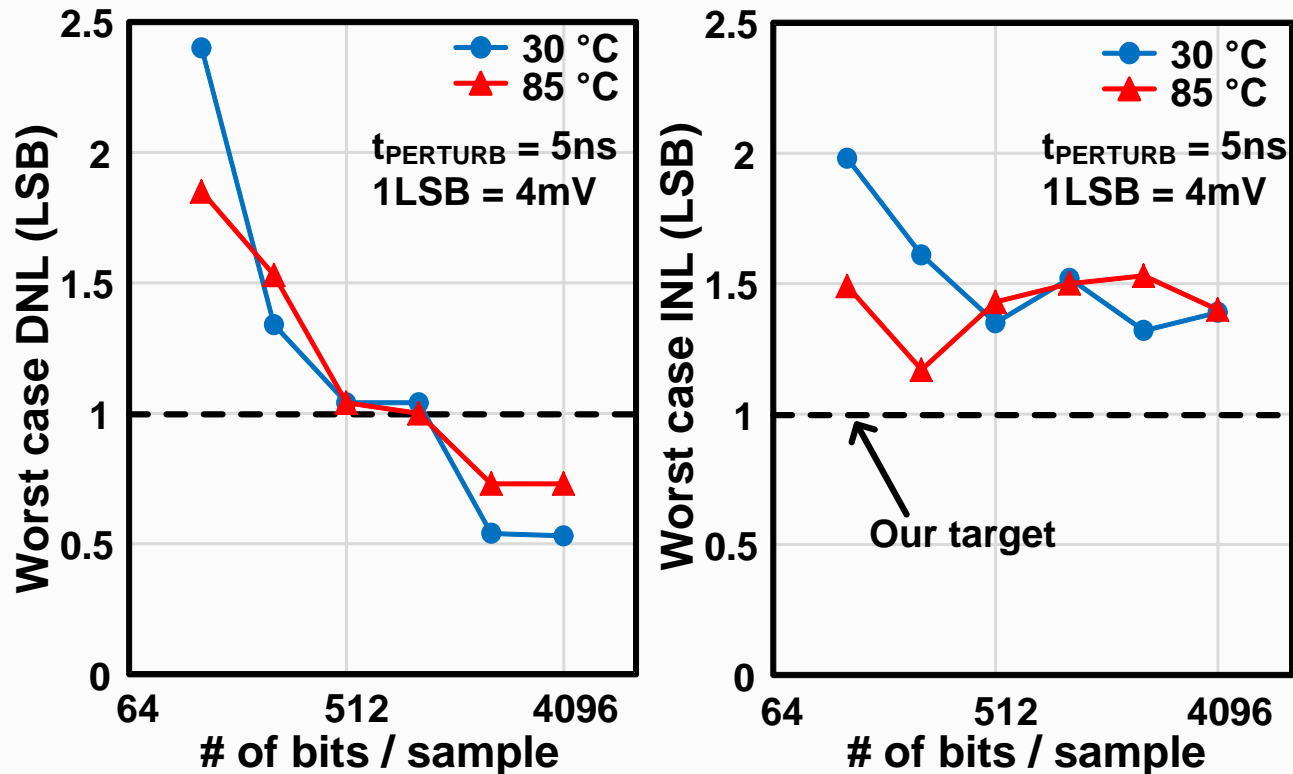
# ADC Non-Linearity Metrics:

## Differential Non-Linearity (DNL)

## Integral Non-Linearity (INL)



# Measured Worst Case DNL and INL

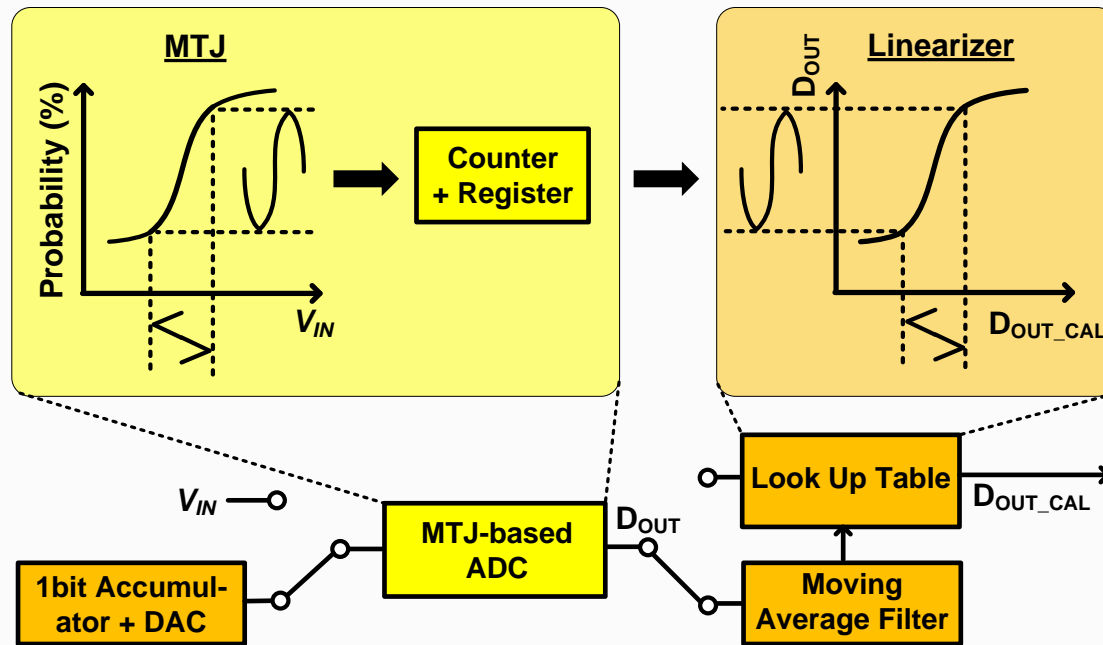


- A 5-bit ADC resolution is assumed (i.e. 1LSB = 4mV)
- DNL of 1 LSB can be achieved by averaging more random bits (e.g. 2,048 bits)
- INL cannot be improved by simply averaging more bits

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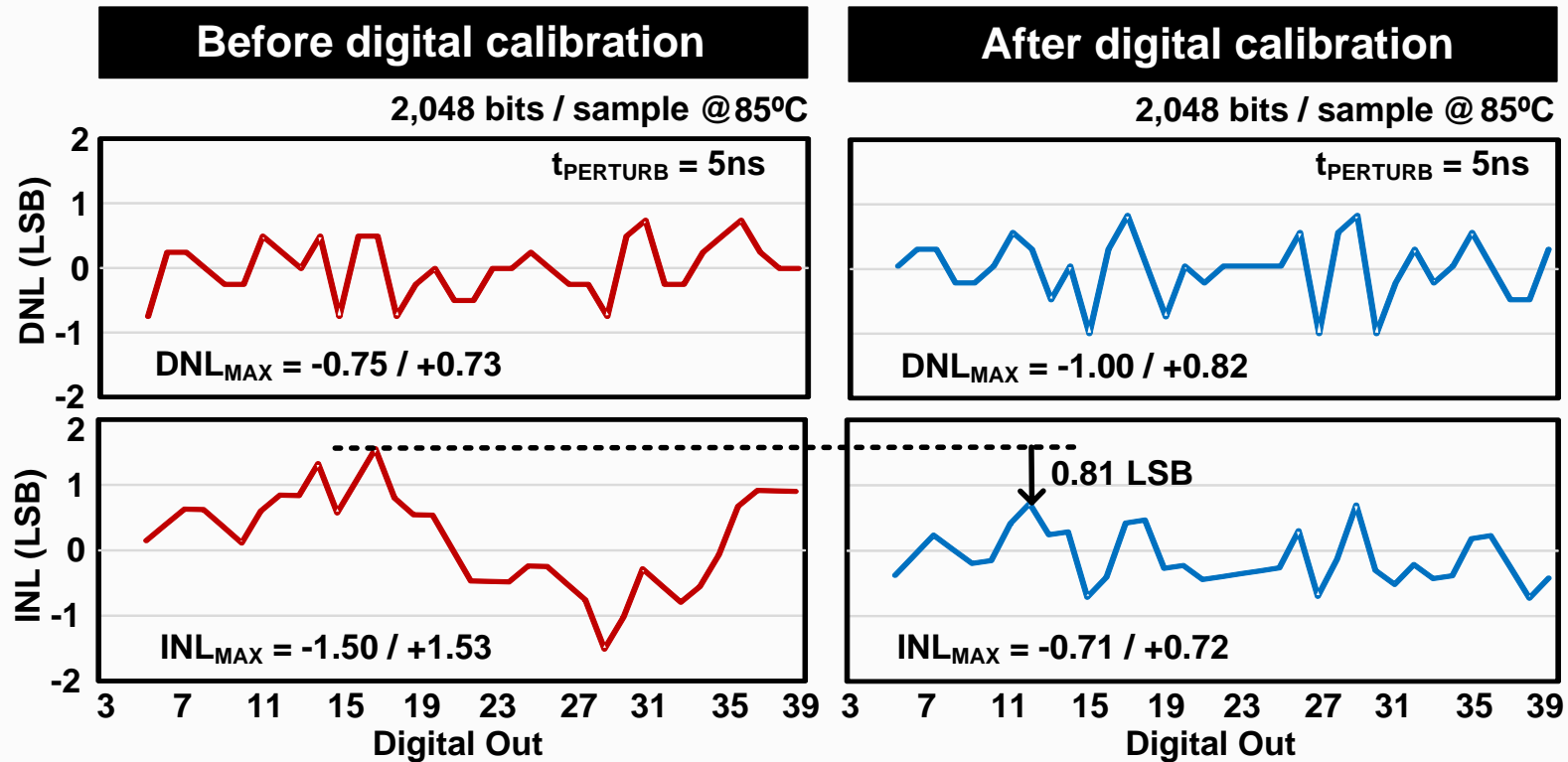
# One-time Digital Calibration for Improving INL



J. Kim, et al., TCAS-I, 2010, J. Daniels, et al., VLSI Circuits Symposium, 2010.

- **Basic idea: Pre-calibrate MTJ transfer curve and store the inverse function in a look-up table to compensate for inherent non-linearity**

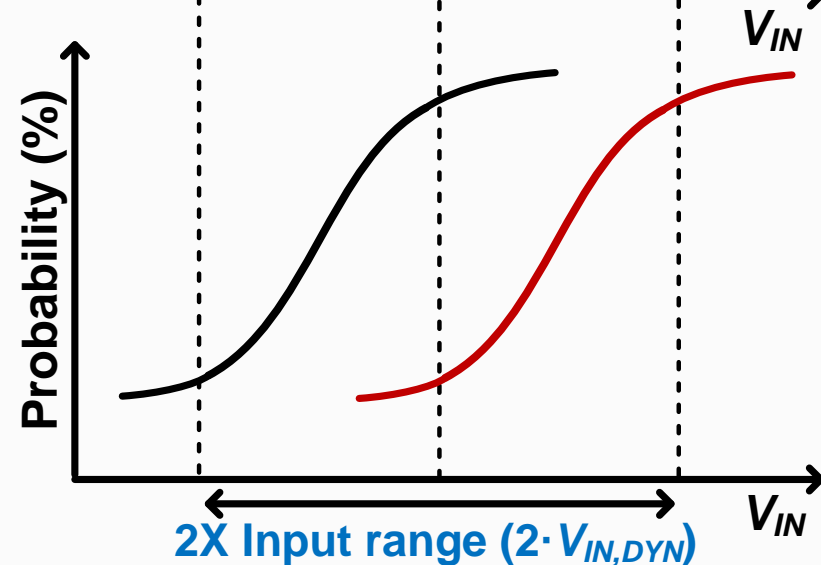
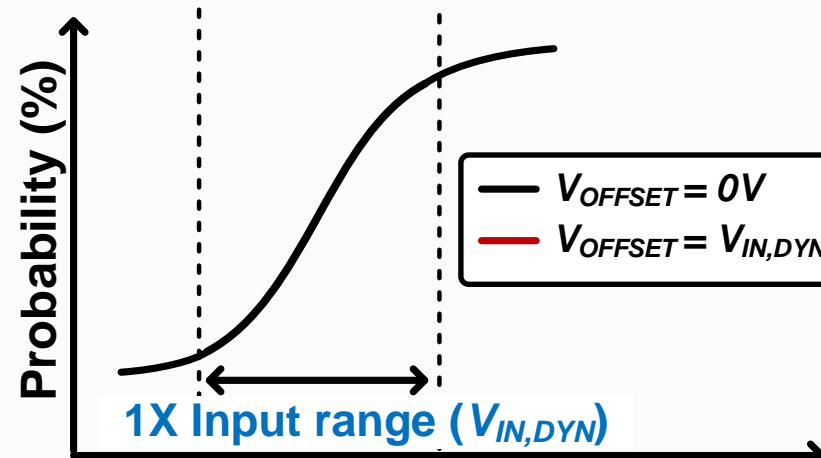
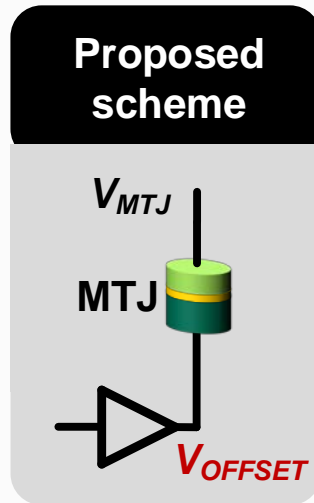
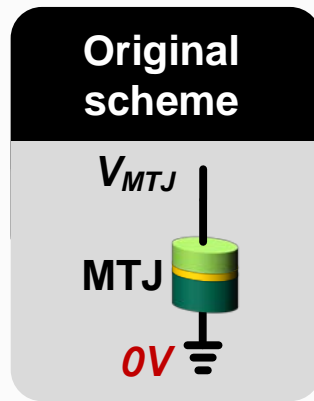
# Measured DNL and INL @ 85 °C



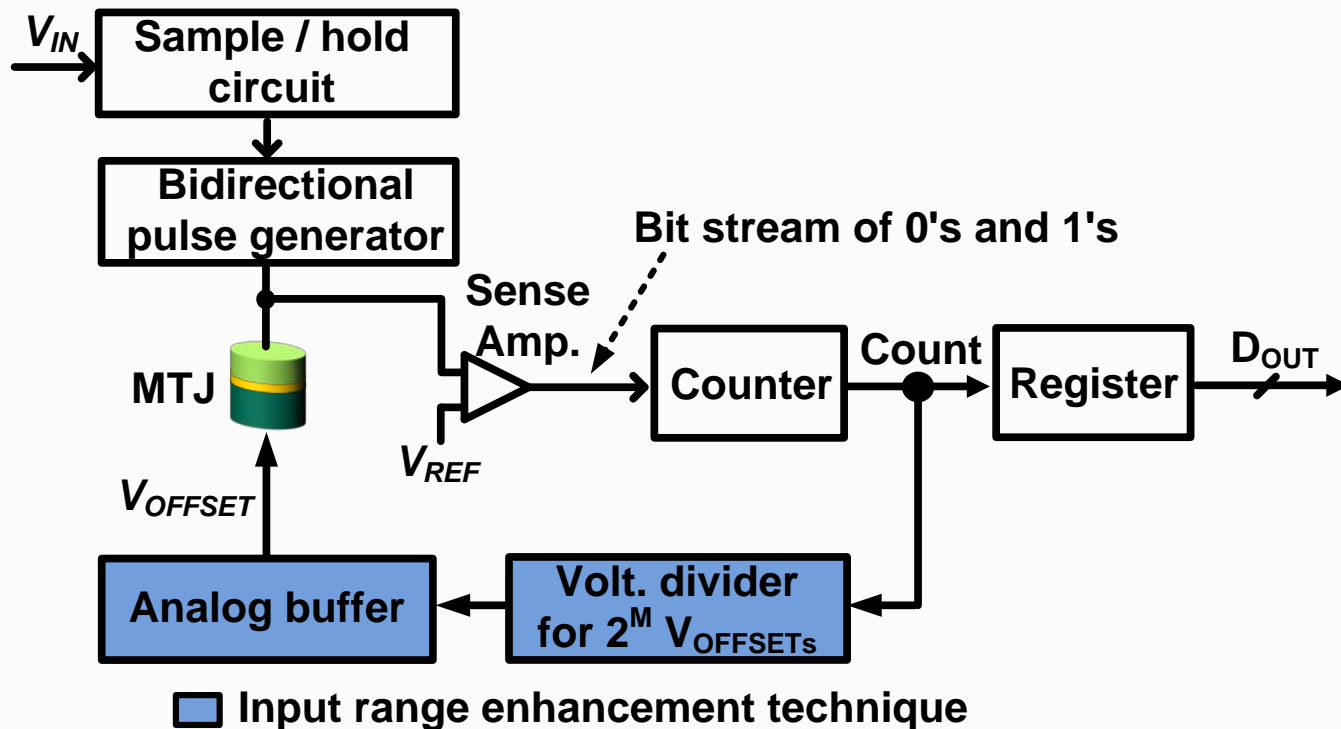
- Target DNL / INL of 1 LSB can be met after one-time calibration
- ADC resolution limited to 5-bit due to narrow input voltage range



# Proposed Input Range Enhancement Technique

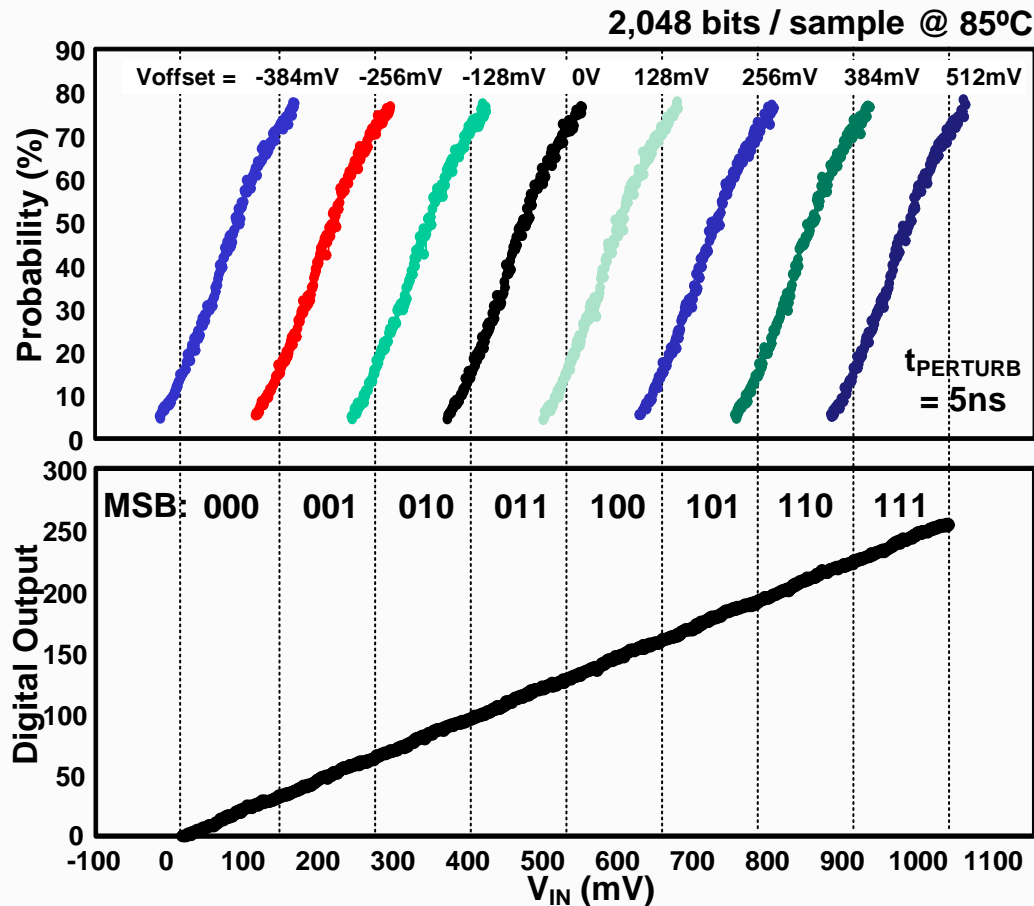


# Implementation of Input Range Enhancement Technique



- A voltage divider and an analog buffer control the MTJ bottom node voltage

# Measured Probability and Corresponding Digital Output

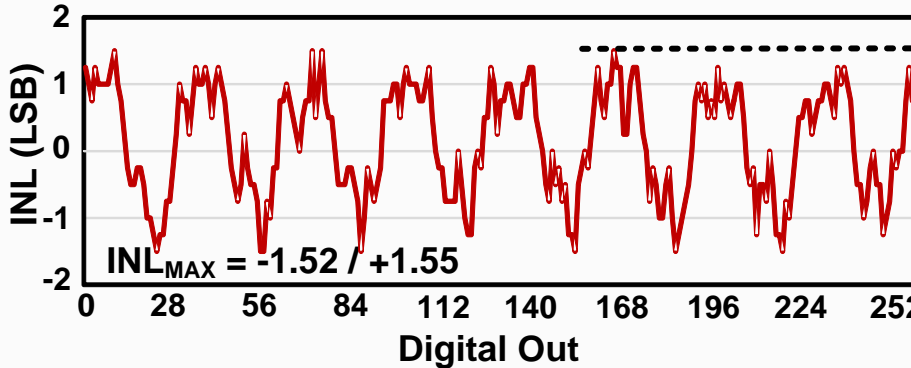
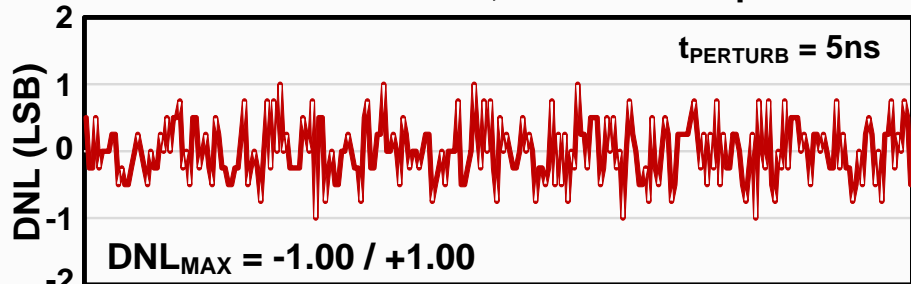


- 8x wider input voltage range  $\rightarrow$  3 additional bits

# Measured DNL and INL @ 85 °C

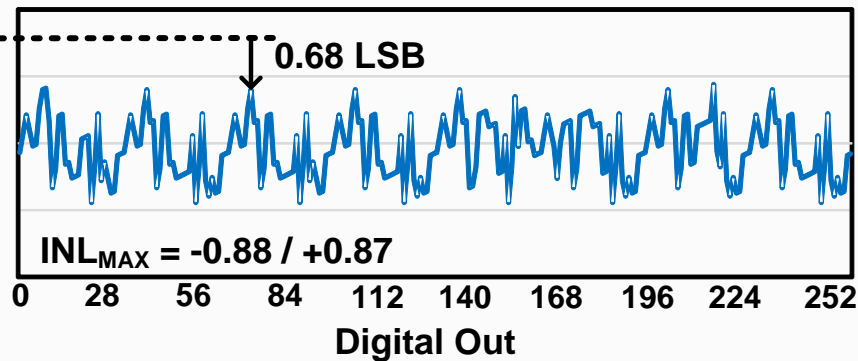
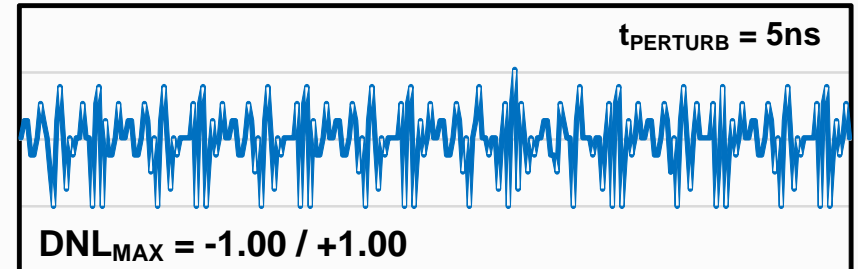
**Before digital calibration**

2,048 bits / sample @ 85°C



**After digital calibration**

2,048 bits / sample @ 85°C



- Target DNL / INL of 1 LSB can be met after calibration
- 8-bit ADC resolution with good linearity is achieved

# ADC Performance Summary

2,048 bits / sample

	Input range	30 °C			85 °C		
		DNL <sub>MAX</sub> (LSB)	INL <sub>MAX</sub> (LSB)	Bits	DNL <sub>MAX</sub> (LSB)	INL <sub>MAX</sub> (LSB)	Bits
Original MTJ-based ADC	128mV (X1)	0.74	1.32	5	0.75	1.53	5
+ Digital calibration	128mV (X1)	1.00	0.76	5	1.00	0.72	5
+ Digital calibration + Input range enhancement	1024mV (X8)	1.00	0.84	8	1.00	0.88	8

- **ADC resolution (=8 bit) was limited by the minimum voltage step (=1mV) of pulse generator. Actual resolution could be as high as 14 bits.**

# Summary

- **An 8-bit resolution MTJ-based ADC with excellent linearity demonstrated for the first time**
  - 2,048 bits averaged to generate one ADC sample
  - Insensitive to temperature using a 5ns pulse width
  - Digital calibration and input range enhancement techniques

## Acknowledgement

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